Time: 3 hours

Reg. No:

SIDDHARTH INSTITUTE OF ENGINEERING & TECHNOLOGY .: PUTTUR

(AUTONOMOUS)

B.Tech II Year I Semester Supplementary Examinations June 2019

BASIC ELECTRONIC DEVICES

(ECE, EEE)

Max. Marks: 60

R16

(Answer all Five Units $5 \times 12 = 60$ Marks)

	UNIT-I	
1	a Derive the expression for diffusion capacitance of a PN junction d	iode. 6M
	b Calculate the dynamic forward and reverse resistance of PN Juncti	on silicon diode 6M
	when the applied voltage is 0.2V at $T = 300^{\circ}$ K with given Io= 2µA	L
•	OR	
2	2 a With neat sketches explain the forward and reverse biasing of a PP	N Junction diode. 6M
	And draw its v-1 Characteristics.	6M
		UIVI
3	3 a Explain in detail about IP Emitters and mention its applications	8M
5	b Comparison between LED and LCD	4M
	OR	11/1
4	a Write notes on TRIAC, DIAC and SCR.	6M
	b Describe in detail about the working principle and characteristics of	of UJT with neat 6M
	sketces.	
	UNIT-III	
5	a Define Rectification efficiency and derive expression for it for the	following 8M
	(i) Half wave rectifier. (ii) Full wave rectifier (iii) Brid	dge rectifier
	b Compare the different types of filter circuits in terms of ripple fact	tors 4M
6	OK A Half wave rectifier has a load of 3 5kO. If the diode resistance	and the secondary 12M
U	coil. Resistance together have resistance of 800Ω and the input voltage of 240V.	
	Calculate (i) Peak, Average and RMS value of the current flowing,	
	(ii) DC Power output,	
	(iii) AC Power input and	
	(iv) Efficiency of the rectifier	
	UNIT-IV	
7	a Draw the circuit diagram for finding the CC characteristics of a Tr	ansistor. 7M
	b Draw the Eber-moll model of a transistor.	5M
0	UR With the halp of past diagram explain the operation and character	istics of n channel 9M
0	enhancement type MOSEET	isues of in-channel olvi
	b Give the comparison between JFET and MOSFET.	4M
	UNIT-V	
9	a What is the necessity of Biasing circuits? Derive the expression fo	r stability factor of 8M
	self bias circuit.	2
	b With neat diagram, explain Voltage Divider Bias Circuit for JFET	. 4M
	OR	
10	0 a Discuss about Thermal Runaway and Thermal Resistance.	6M
	b Explain Collector to Base bias of a Transistor with neat circuit dia	gram 6M

*** END ***